

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

# 2SA1941

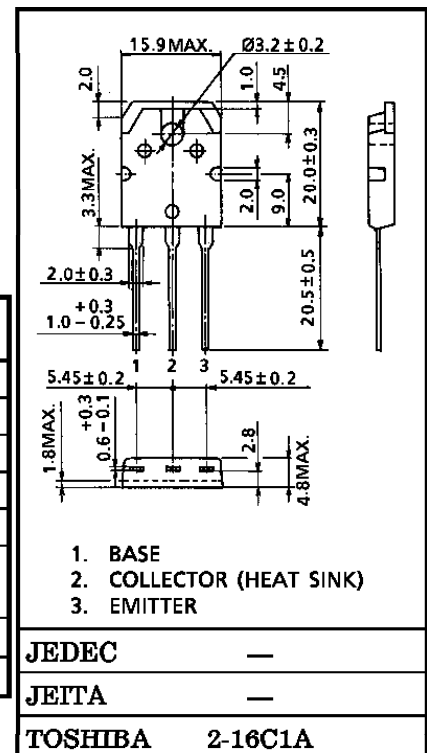
POWER AMPLIFIER APPLICATIONS

- Complementary to 2SC5198
- Recommend for 70W High Fidelity Audio Frequency Amplifier Output Stage

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	-140	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-140	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current	I <sub>C</sub>	-10	A
Base Current	I <sub>B</sub>	-1	A
Collector Power Dissipation (Tc = 25°C)	P <sub>C</sub>	100	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C

Unit in mm



Weight : 4.7g (Typ.)

ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> = -140V, I <sub>E</sub> = 0	—	—	-5.0	μA
Emitter Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0	—	—	-5.0	μA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I <sub>C</sub> = -50mA, I <sub>B</sub> = 0	-140	—	—	V
DC Current Gain	h <sub>FE</sub> (1) (Note)	V <sub>CE</sub> = -5V, I <sub>C</sub> = -1A	55	—	160	
	h <sub>FE</sub> (2)	V <sub>CE</sub> = -5V, I <sub>C</sub> = -5A	35	83	—	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -7A, I <sub>B</sub> = -0.7A	—	-0.8	-2.0	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -5A	—	-1.0	-1.5	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -1A	—	30	—	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz	—	320	—	pF

(Note) : h<sub>FE</sub> (1) Classification R : 55~110, O : 80~160

